

Laser-induced desorption from silicon (111) surfaces with adsorbed chlorine atoms

This article has been downloaded from IOPscience. Please scroll down to see the full text article.

1997 J. Phys.: Condens. Matter 9 1391

(<http://iopscience.iop.org/0953-8984/9/6/023>)

View [the table of contents for this issue](#), or go to the [journal homepage](#) for more

Download details:

IP Address: 171.66.16.151

The article was downloaded on 12/05/2010 at 23:05

Please note that [terms and conditions apply](#).

Erratum

Laser-induced desorption from silicon (111) surfaces with adsorbed chlorine atoms

K Hattori, K Shudo, T Iimori, F Komori and Y Murata 1996 *J. Phys.: Condens. Matter* 8 6543–6551

Due to a printing error, the wrong figure 2 appeared in this paper. The correct figure is reproduced below. The World Wide Web version of the paper contains the *correct* figure 2.

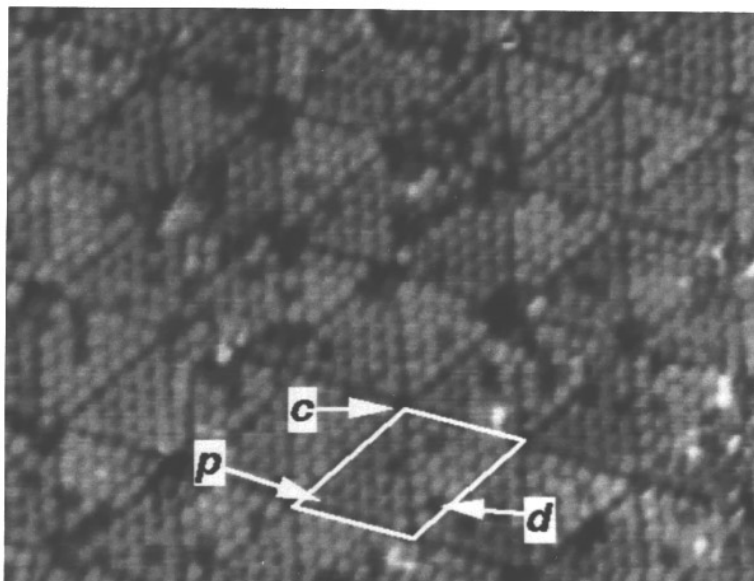


Figure 2. An STM image obtained after irradiation with laser pulses of a chlorine-saturated Si(111) surface [14]. The photon energy is 4.7 eV and the sample bias voltage is +3.0 V. A white rhombic indicator shows a unit cell surrounded by corner holes ('c') and dimers. Bright spherical protrusions ('p') on an atomic scale are 7×7 ordered as the Si rest atoms of the DAS model. A number of depressions ('d') are found on the surface especially around corner holes and dimers.

In addition, referring to figure 1, the third sentence of the second paragraph of the Introduction should read:

A unit cell in the DAS model includes 12 adatoms (large solid circles), 42 rest atoms (small solid circles), 9 dimers, and 1 corner hole.